

Silicon NPN Power Transistors

BUS13A

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	9	V
I_C	Collector current		15	A
I_{CM}	Collector current-Peak		30	A
I_B	Base current		6	A
I_{BM}	Base current-Peak		9	A
P_T	Total power dissipation	$T_{mb} = 25\square$	175	W
T_j	Junction temperature		200	$\square$
T_{stg}	Storage temperature		-65~200	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-mb}$	Thermal resistance from junction to mounting base	1.0	$\square/W$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.1A$; $I_B=0$; $L=25mH$	450			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=8A$; $I_B=1.6A$			1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=8A$; $I_B=1.6A$			1.6	V
I_{CES}	Collector cut-off current	$V_{CE}=RatedBV_{CEO}$; $V_{BE}=0$ $T_C=125^\circ C$			1 4	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=9V$; $I_C=0$			10	mA
h_{FE}	DC current gain	$I_C=1A$; $V_{CE}=5V$	15		50	

Switching times

t_{on}	Turn-on time	$I_C=8A$; $I_{B1}=-I_{B2}=1.6A$			1.0	μs
t_s	Storage time				4.0	μs
t_f	Fall time				0.8	μs

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PACKAGE OUTLINE

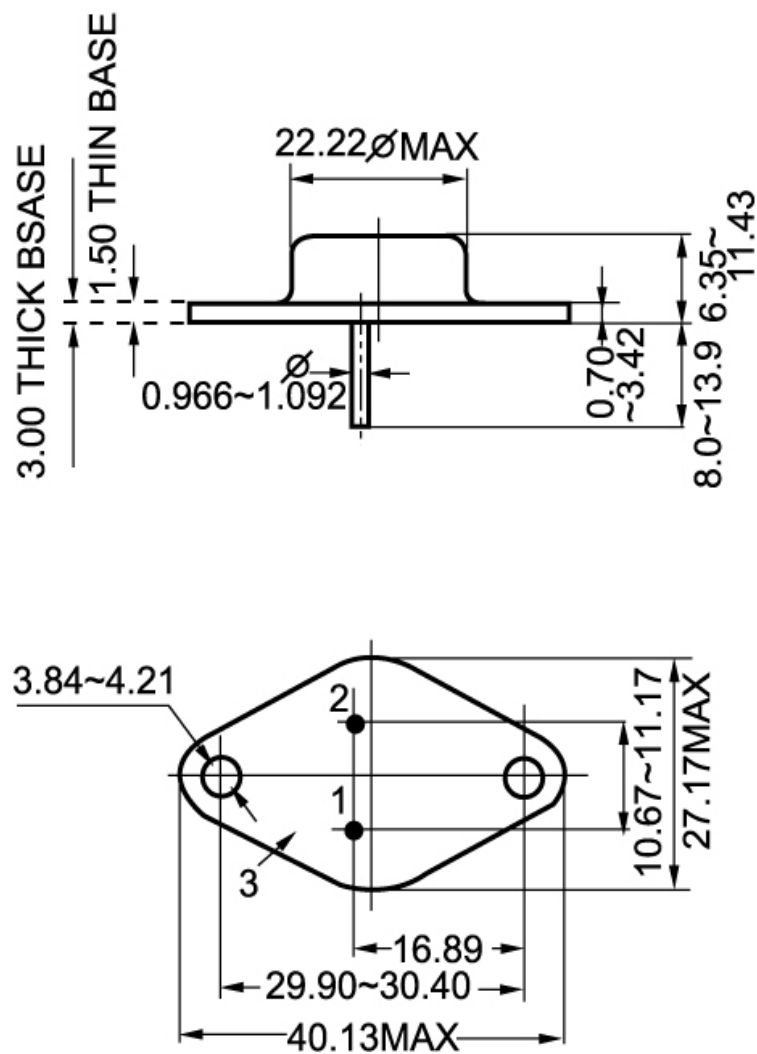
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Fig.2 Outline dimensions